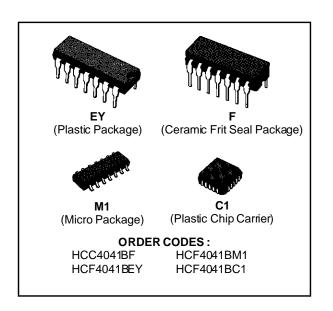


HCC/HCF4041UB

QUAD TRUE/COMPLEMENT BUFFER

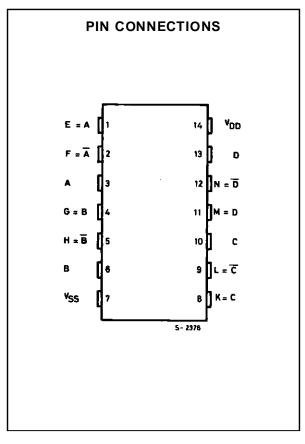
- BALANCED SINK AND SOURCE CURRENT;
 APPROXIMATELY 4 TIMES STANDARD "B"
 DRIVE
- EQUALIZED DELAY TO TRUE AND COMPLE-MENT OUTPUTS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100 % TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDECTEN-TATIVE STANDARD N° 13A, "STANDARD SPE-CIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



DESCRIPTION

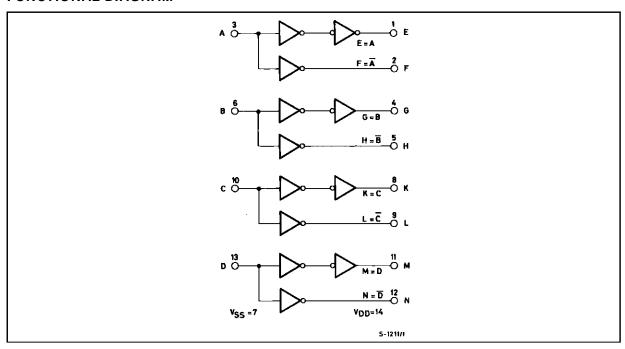
The **HCC4041UB** (extended temperature range) and **HCF4041UB** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micro package.

The HCC/HCF4041UB types are quad true/complement buffers consisting of n- and p-channel units having low channel resistance and high current (sourcing and sinking) capability. The HCC/-HCF4041UB is intended for use as a buffer, line driver, or COS/MOS-to-TTL driver. It can be used as an ultra-low power resistor-network driver for A/D and D/A conversion, as a transmission-line driver, and in other applications where high noise immunity and low-power dissipation are primary design requirements.



June 1989 1/12

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
Vi	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I_1	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package-temperature Range	200	mW mW
Top	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

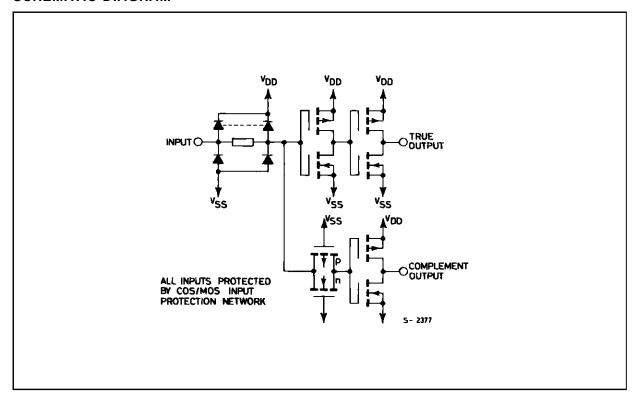
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability. * All voltage values are referred to Vss pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage: HCC Types	3 to + 18	V
	HCF Types	3 to + 15	V
V_{I}	Input Voltage	0 to V _{DD}	V
Top	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	oိ oိ



SCHEMATIC DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

			Т	est Con	dition	s	Value							
Symbol	Parameter		٧ı	٧o	I ₀	V _{DD}	ΤL	o w*		25°C		T _{Hi}	igh [*]	Unit
			(V)	(V)	(μA)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
ΙL	Quiescent		0/ 5			5		1		0.02	1		30	
	Current	HCC	0/10			10		2		0.02	2		60	
		Types	0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	μΑ
			0/ 5			5		4		0.02	4		30	
		HCF Types	0/10			10		8		0.02	8		60	
			0/15			15		16		0.02	16		120	
V _{OH}	Output High	h	0/ 5		< 1	5	4.95		4.95			4.95		
	Voltage		0/10		< 1	10	9.95		9.95			9.95		V
			0/15		< 1	15	14.95		14.95			14.95		
V _{OL}	Output Low	ı	5/0		< 1	5		0.05			0.05		0.05	
	Voltage		10/0		< 1	10		0.05			0.05		0.05	V
			15/0		< 1	15		0.05			0.05		0.05	
V _{IH}	/ _{IH} Input High			0.5/4.5	< 1	5	4		4			4		
	Voltage		1/9	< 1	10	8		8			8		V	
				1.5/13.5	< 1	15	12.5		12.5			12.5		

^{*} $T_{Low} = -55^{\circ}C$ for HCC device : $-40^{\circ}C$ for HCF device. * $T_{High} = +125^{\circ}C$ for HCC device : $+85^{\circ}C$ for HCF device. The Noise Margin for both "1" and "0" level is : 1V min. with $V_{DD} = 5V$, 2V min. with $V_{DD} = 10V$, 2.5V min. with $V_{DD} = 15V$.



STATIC ELECTRICAL CHARACTERISTICS (continued)

			Т	est Con	dition	s				Value				
Symbol	Parame	eter	٧ı	٧o	I ₀	V_{DD}	ΤL	o w*		25°C		T Hi	gh [*]	Unit
			(V)	(V)	(μA)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
V_{IL}	Input Low			4.5/0.5	< 1	5		1			1		1	
	Voltage			9/1	< 1	10		2			2		2	V
				13.5/1.5	< 1	15		2.5			2.5		2.5	
I _{OH}	Output		0/ 5	2.5		5	- 8.4		- 6.4	– 12.8		- 4.6		
	Drive Current	HCC	0/ 5	4.6		5	- 2.1		- 1.6	- 3.2		- 1.2		
	Cullent	Types	0/10	9.5		10	- 6.25		- 5	- 10		- 3.5		
			0/15	13.5		15	- 24		- 19	- 38		- 13		mA
			0/ 5	2.5		5	- 6.8		- 5.44	- 12.8		- 4.08		1117 (
	HCF	HCF	0/ 5	4.6		5	- 1.7		- 1.36	- 3.2		- 1.02		
		Types	0/10	9.5		10	- 5.31		- 4.25	- 10		- 3.18		
			0/15	13.5		15	-20.18		-16.15	- 38		-12.11		
I _{OL}	Output	1100	0/ 5	0.4		5	2.1		1.6	3.2		1.2		
	Sink Current	HCC Types	0/10	0.5		10	6.25		5	10		3.5		
	Cullent	.) poo	0/15	1.5		15	24		19	38		13		
			0/ 5	0.4		5	1.7		1.36	3.2		1.02		
		HCF Types	0/10	0.5		10	5.31		4.25	10		3.18		
		.) 00	0/15	1.5		15	20.18		16.15	38		12.11		
I _{IH} , I _{IL}	Input HCC leakage Types	0/18	Any In	nut	18		± 0.1		±10 ⁻⁵	± 0.1		± 1	•	
	Current	HCF Types	0/15	Ally III	pui	15		± 0.3		±10 ⁻⁵	± 0.3		± 1	± 1
Cı	Input Ca	apacitano	е	Any In	put					15	22.5			pF

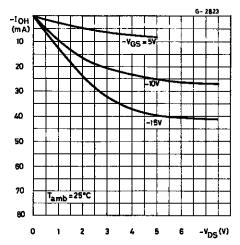
DYNAMIC ELECTRICAL CHARACTERISTICS (T $_{amb}$ = 25°C, C $_{L}$ = 50pF, R $_{L}$ = 200k Ω , typical temperature coefficient for all V $_{DD}$ values is 0.3 %/°C, all input rise and fall times = 20ns)

Comple at	Domenton	Test Conditions		I I m i 4			
Symbol	Parameter		V_{DD} (V)	Min.	Тур.	Max.	Unit
t _{PLH} , t _{PHL}	Propagation Delay Time		5		60	120	
			10		35	70	ns
			15		25	50	
t _{THL} , t _{TLH}	Transition Time		5		40	80	
			10		20	40	ns
			15		15	30	

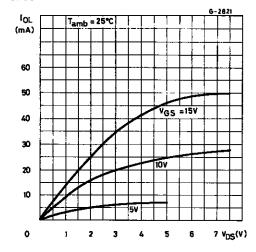
^{*} $T_{Low} = -55^{\circ}C$ for **HCC** device : $-40^{\circ}C$ for **HCF** device. * $T_{High} = +125^{\circ}C$ for **HCC** device : $+85^{\circ}C$ for **HCF** device.

The Noise Margin for both "1" and "0" level is : 1V min. with $V_{DD} = 5V$, 2V min. with $V_{DD} = 10V$, 2.5V min. with $V_{DD} = 15V$.

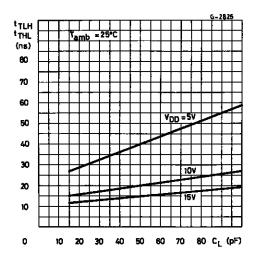
Minimum Output High (source) Current Characteristics.



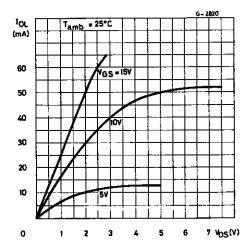
Minimum Output Low (sink) Current Characteristics.



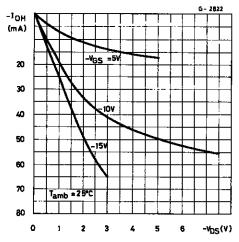
Typical Transition Time vs. Load Capacitance.



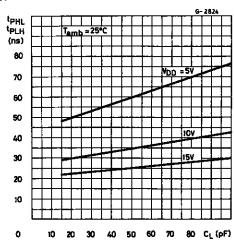
Typical Output Low (sink) Current.



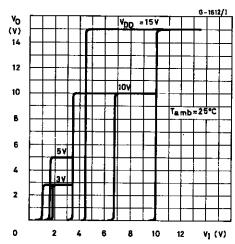
Typical Output High (source) Current Characteristics.

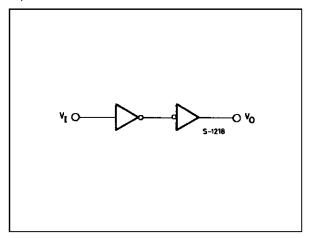


Typical Propagation Delay Time vs. Load Capacitance.

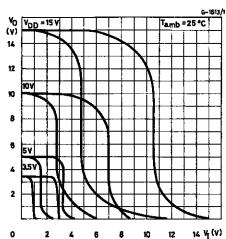


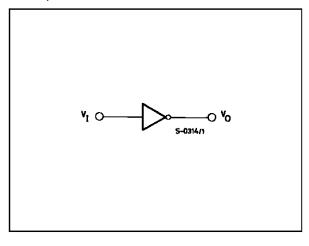
Minimum and Maximum Transfer Characteristics-true Output-and Test Circuit.



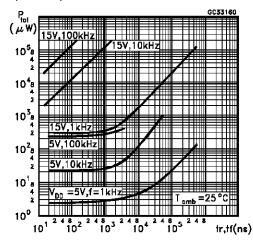


Minimum Maximum Transfer Characteristics Complement Output-and Test Circuit.

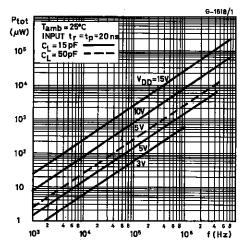




Typical Power Dissipation vs. Input Rise and Fall Time per Output Pair.

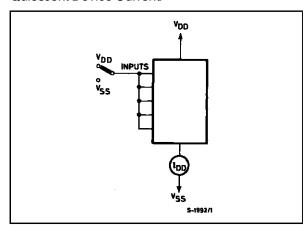


Typical Power Dissipation vs. Frequency per Output Pair.

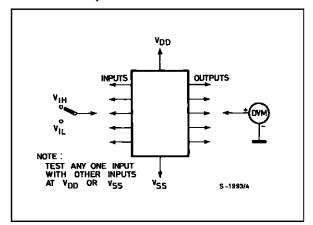


TEST CIRCUITS

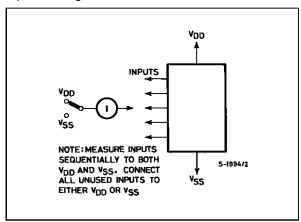
Quiescent Device Current.



Noise Immunity.

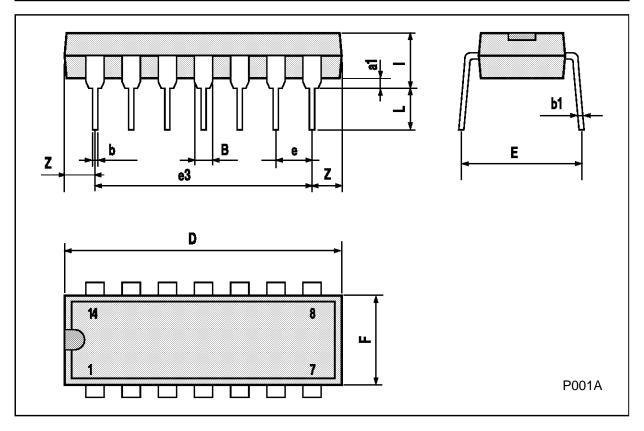


Input Leakage Current.



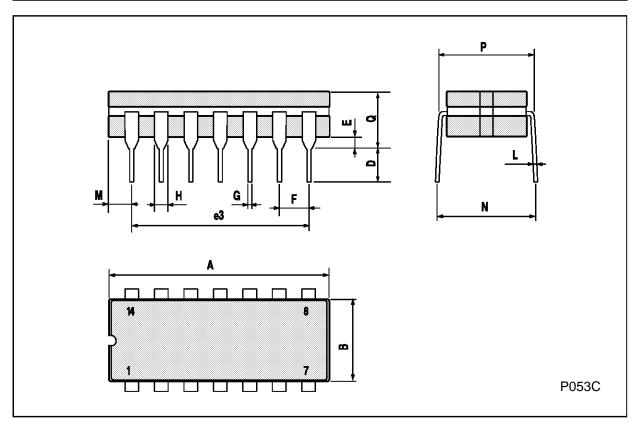
Plastic DIP14 MECHANICAL DATA

DIM.		mm		inch				
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	1.39		1.65	0.055		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		15.24			0.600			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z	1.27		2.54	0.050		0.100		



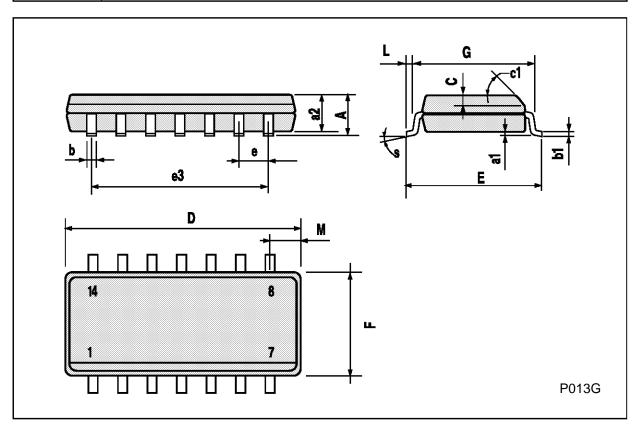
Ceramic DIP14/1 MECHANICAL DATA

DIM.		mm		inch				
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Α			20			0.787		
В			7.0			0.276		
D		3.3			0.130			
E	0.38			0.015				
e3		15.24			0.600			
F	2.29		2.79	0.090		0.110		
G	0.4		0.55	0.016		0.022		
Н	1.17		1.52	0.046		0.060		
L	0.22		0.31	0.009		0.012		
М	1.52		2.54	0.060		0.100		
N			10.3			0.406		
Р	7.8		8.05	0.307		0.317		
Q			5.08			0.200		



SO14 MECHANICAL DATA

DIM.		mm		inch				
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)				
D	8.55		8.75	0.336		0.344		
E	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		7.62			0.300			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.68			0.026		
S			8° (r	max.)				



PLCC20 MECHANICAL DATA

DIM.		mm		inch				
Diiii.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А	9.78		10.03	0.385		0.395		
В	8.89		9.04	0.350		0.356		
D	4.2		4.57	0.165		0.180		
d1		2.54			0.100			
d2		0.56			0.022			
E	7.37		8.38	0.290		0.330		
е		1.27			0.050			
e3		5.08			0.200			
F		0.38			0.015			
G			0.101			0.004		
М		1.27			0.050			
M1		1.14			0.045			



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